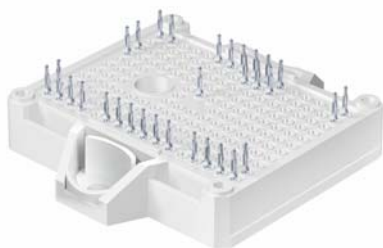


SK225GH07H5TD1E2



SEMITOP®E2

H-Bridge

Engineering Sample SK225GH07H5TD1E2

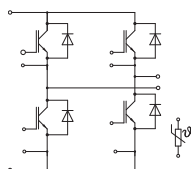
Target Data

Features*

- Optimized design for superior thermal performances
- Low inductive design
- Press-Fit contact technology
- 650V Trench5 IGBT (H5)
- Rapid switching diode technology
- Integrated NTC temperature sensor
- UL recognized file no. E 63 532

Typical Applications

- Electric Vehicle charging
- Switched Mode Power Supply
- Welding



GH-T

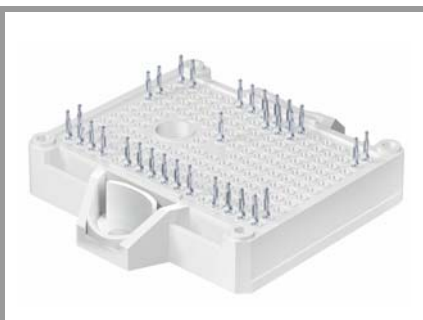
Absolute Maximum Ratings

Symbol	Conditions	Values	Unit	
Inverter - IGBT				
V_{CES}	$T_j = 25\text{ °C}$	650	V	
I_C	$\lambda_{paste}=0.8\text{ W/(mK)}$	$T_s = 25\text{ °C}$	162	A
	$T_j = 175\text{ °C}$	$T_s = 70\text{ °C}$	126	A
I_C	$\lambda_{paste}=2.5\text{ W/(mK)}$	$T_s = 25\text{ °C}$	215	A
	$T_j = 175\text{ °C}$	$T_s = 70\text{ °C}$	169	A
I_{Cnom}		225	A	
I_{CRM}		450	A	
V_{GES}		-20 ... 20	V	
t_{psc}	$V_{CC} = 360\text{ V}$ $V_{GE} \leq 15\text{ V}$ $V_{CES} \leq 650\text{ V}$	$T_j = 150\text{ °C}$	μs	
T_j		-40 ... 175	$^{\circ}\text{C}$	
Inverse - Diode				
I_F	$\lambda_{paste}=0.8\text{ W/(mK)}$	$T_s = 25\text{ °C}$	63	A
	$T_j = 175\text{ °C}$	$T_s = 70\text{ °C}$	49	A
I_F	$\lambda_{paste}=2.5\text{ W/(mK)}$	$T_s = 25\text{ °C}$	75	A
	$T_j = 175\text{ °C}$	$T_s = 70\text{ °C}$	59	A
I_{FRM}		150	A	
I_{FSM}	$t_p = 10\text{ ms, sin } 180^{\circ}, T_j = 150\text{ °C}$	380	A	
T_j		-40 ... 175	$^{\circ}\text{C}$	
Module				
$I_{t(RMS)}$	$\Delta T_{terminal}$ at PCB joint = 30 K, per pin	30	A	
T_{stg}		-40 ... 125	$^{\circ}\text{C}$	
V_{isol}	AC, sinusoidal, $t = 1\text{ min}$	2500	V	

Characteristics

Symbol	Conditions	min.	typ.	max.	Unit
Inverter - IGBT					
$V_{CE(sat)}$	$I_C = 225\text{ A}$ $V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25\text{ °C}$	1.65	2.22	V
		$T_j = 150\text{ °C}$	1.86	2.43	V
V_{CE0}	chipelevel	$T_j = 25\text{ °C}$	1.00	1.28	V
		$T_j = 150\text{ °C}$	0.92	1.20	V
r_{CE}	$V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25\text{ °C}$	2.9	4.2	m Ω
			4.2	5.5	m Ω
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 2.25\text{ mA}$	3.3	4	4.7	V
I_{CES}	$V_{GE} = 0\text{ V}, V_{CE} = 650\text{ V}, T_j = 25\text{ °C}$			1	mA
C_{ies}	$V_{CE} = 25\text{ V}$		12.9		nF
C_{oes}	$V_{GE} = 0\text{ V}$		0.225		nF
C_{res}			0.048		nF
Q_G	$V_{GE} = 0\text{ V} \dots +15\text{ V}$		489		nC
R_{Gint}	$T_j = 25\text{ °C}$		1.6		Ω
$t_{d(on)}$	$V_{CC} = 300\text{ V}$	$T_j = 150\text{ °C}$	t.b.d.		ns
t_r	$I_C = 100\text{ A}$ $R_{G\ on} = 2.2\ \Omega$	$T_j = 150\text{ °C}$	t.b.d.		ns
		$T_j = 150\text{ °C}$	1.85		mJ
E_{on}	$R_{G\ off} = 2.2\ \Omega$	$T_j = 150\text{ °C}$	t.b.d.		ns
$t_{d(off)}$		$T_j = 150\text{ °C}$	t.b.d.		ns
t_f		$T_j = 150\text{ °C}$	t.b.d.		ns
E_{off}	$V_{GE} = +15/-15\text{ V}$	$T_j = 150\text{ °C}$	1.25		mJ
$R_{th(j-s)}$	per IGBT, $\lambda_{paste}=0.8\text{ W/(mK)}$		0.44		K/W
$R_{th(j-s)}$	per IGBT, $\lambda_{paste}=2.5\text{ W/(mK)}$		0.29		K/W

SK225GH07H5TD1E2



SEMITOP®E2

H-Bridge

Engineering Sample SK225GH07H5TD1E2

Target Data

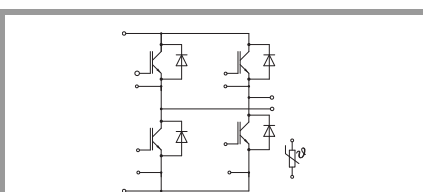
Features*

- Optimized design for superior thermal performances
- Low inductive design
- Press-Fit contact technology
- 650V Trench5 IGBT (H5)
- Rapid switching diode technology
- Integrated NTC temperature sensor
- UL recognized file no. E 63 532

Typical Applications

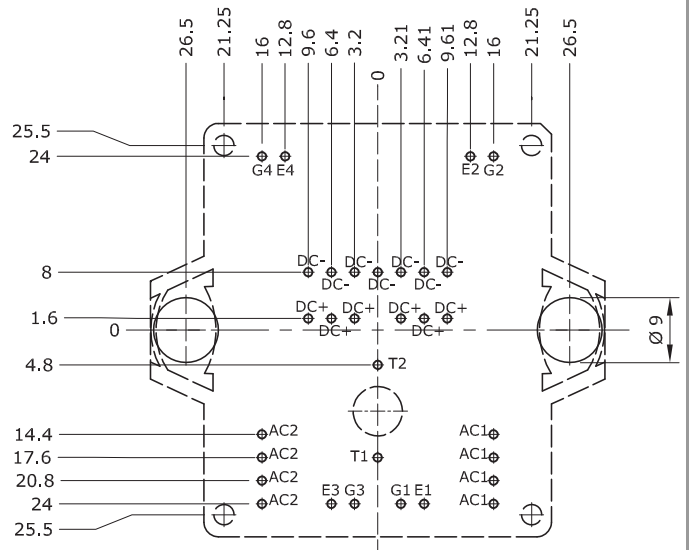
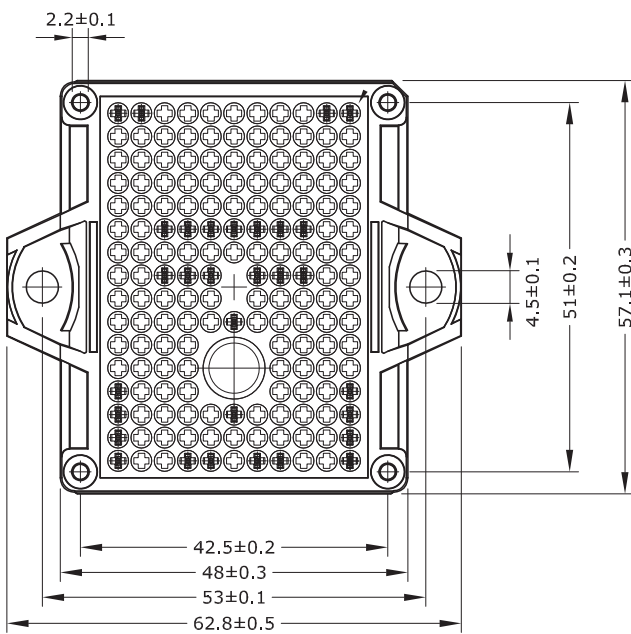
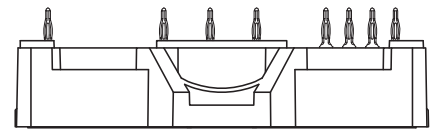
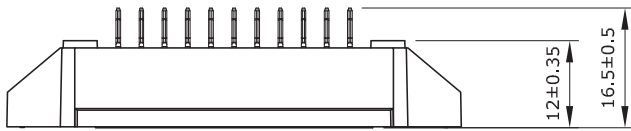
- Electric Vehicle charging
- Switched Mode Power Supply
- Welding

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverse - Diode						
$V_F = V_{EC}$	$I_F = 75\text{ A}$	$T_j = 25\text{ °C}$		1.35	1.92	V
		chipelevel	$T_j = 150\text{ °C}$	1.30	1.89	V
V_{F0}	chipelevel	$T_j = 25\text{ °C}$		0.90	1.10	V
		$T_j = 150\text{ °C}$		0.71	0.94	V
r_F	chipelevel	$T_j = 25\text{ °C}$		6.0	11	mΩ
		$T_j = 150\text{ °C}$		7.9	13	mΩ
I_{RRM}	$I_F = 75\text{ A}$			t.b.d.		A
Q_{rr}	$V_{GE} = -15\text{ V}$ $V_{CC} = 300\text{ V}$			t.b.d.		μC
E_{rr}				0.7		mJ
$R_{th(j-s)}$	per Diode, $\lambda_{paste}=0.8\text{ W/(mK)}$			1.39		K/W
$R_{th(j-s)}$	per Diode, $\lambda_{paste}=2.5\text{ W/(mK)}$			1.06		K/W
Module						
L_{CE}				6		nH
M_s	to heatsink		1.6		2.3	Nm
W				35		g
Temperature Sensor						
R_{100}	$T_c=100\text{ °C}$ ($R_{25}=5\text{ k}\Omega$)			$493 \pm 5\%$		Ω
$B_{100/125}$	$R(T)=R_{100}\exp[B_{100/125}(1/T-1/T_{100})]$; $T[K]$;			3550 $\pm 2\%$		K



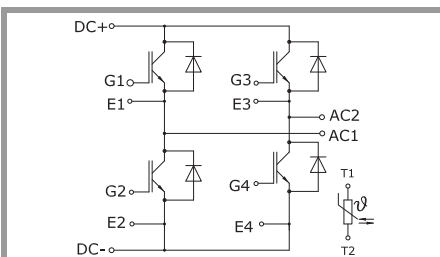
GH-T

SK225GH07H5TD1E2



- Pin-Grid 3.2 mm
- Tolerance of PCB hole pattern $\boxed{\oplus \text{ } \varnothing 0.1}$
- Diameters of drill $\varnothing 1.15\text{mm}$
- Copper thickness in hole 25 - 50 μm
- Hole specification for contacts:
refer to SEMITOP E1/E2 Mounting Instruction

SEMITOP®E2



GH-T

This is an electrostatic discharge sensitive device (ESDS) due to international standard IEC 61340.

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